

Vishay Siliconix

RoHS

COMPLIANT HALOGEN

FREE

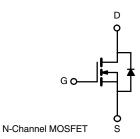
Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0018			
I _D (A)	200			
Configuration	Single			
Package	TO-263-7L			



FEATURES

- TrenchFET[®] power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified ^d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \degree C$, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V _{DS}	40	v		
Gate-Source Voltage	V _{GS}	± 20	v			
Continuous Drain Current	T _C = 25 °C ^a	I	200			
	T _C = 125 °C	ID	192			
Continuous Source Current (Diode Conducti	I _S	200	A			
Pulsed Drain Current ^b	I _{DM}	600				
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	85			
Single Pulse Avalanche Energy	L = 0.1 min	E _{AS}	361	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C	PD	375	w		
	T _C = 125 °C	гD	125	vv		
Operating Junction and Storage Temperatur	T _J , T _{stg}	-55 to +175	°C			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	0/10	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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SPECIFICATIONS ($T_C = 25 \degree C$,	unless otherv	vise noted)					
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static	•			•		•	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		40	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	2.5	3.0	3.5	v
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	200	-	-	А
		V _{GS} = 10 V	I _D = 30 A	-	0.0015	0.0018	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 30 A, T _J = 125 °C	-	-	0.0028	Ω
		$V_{GS} = 10 V$	I _D = 30 A, T _J = 175 °C	-	-	0.0034	
Forward Transconductance ^b	9 _{fs}	V _{DS}	= 15 V, I _D = 30 A	-	198	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	13 880	17 350	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz		1414	1770	pF
Reverse Transfer Capacitance	C _{rss}			-	840	1050	1
Total Gate Charge ^c	Qg			-	206	310	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 120 \text{ A}$	-	50	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	44	-	
Gate Resistance	Rg	f = 1 MHz		0.25	0.8	1.8	Ω
Turn-On Delay Time ^c	t _{d(on)}				26	39	
Rise Time ^c	tr	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 20 \; V, \; R_{\text{L}} = 0.17 \; \Omega \\ I_{\text{D}} \cong 120 \; A, \; V_{\text{GEN}} = 10 \; V, \; R_{\text{g}} = 1 \; \Omega \end{array}$		-	21	32	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	68	102	
Fall Time ^c	t _f			-	12	18	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	600	А
Forward Voltage	V _{SD}	I _F = 80 A, V _{GS} = 0 V		-	0.86	1.5	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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 $V_{GS} = 6 V$

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V_{GS} = 10 V thru 7 V

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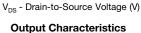
250

200

150

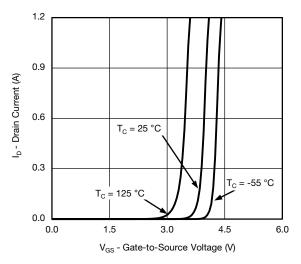
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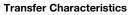
I_D - Drain Current (A)

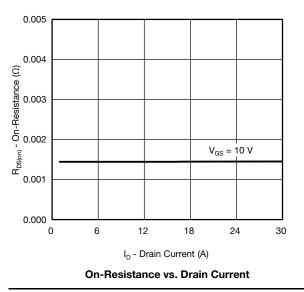


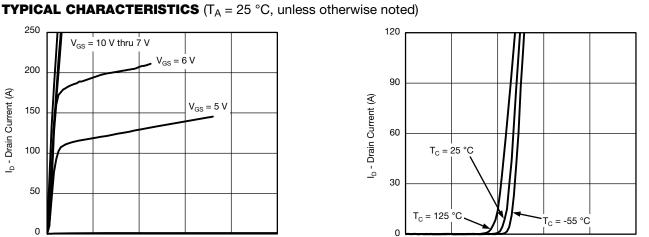
6

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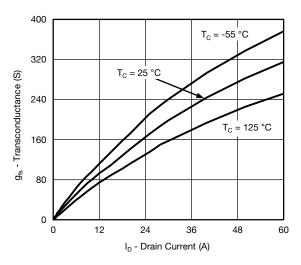
V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**

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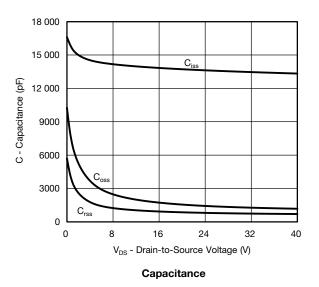
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S15-1874-Rev. B, 10-Aug-15

3

Document Number: 67184

SQM200N04-1m8

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-25

0.7

0.2

-0.3

-0.8

-1.3

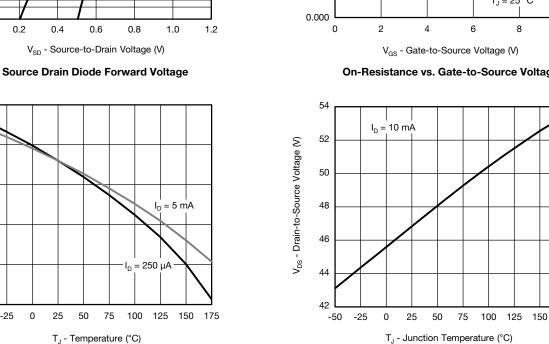
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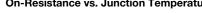
-50

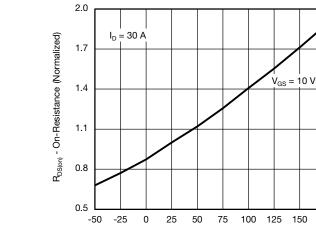
V_{GS(th)} Variance (V)

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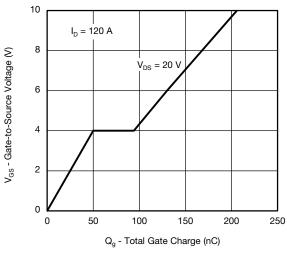


SQM200N04-1m8

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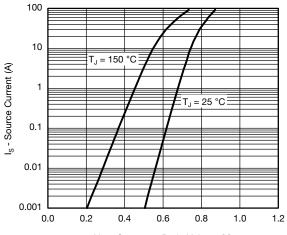
175

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



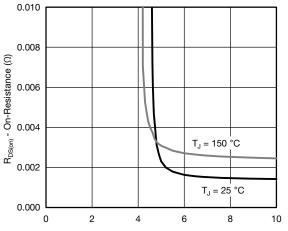
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Gate Charge



Threshold Voltage

T_J - Junction Temperature (°C) **On-Resistance vs. Junction Temperature**



On-Resistance vs. Gate-to-Source Voltage

150 175 T_J - Junction Temperature (°C) Drain Source Breakdown vs. Junction Temperature

Document Number: 67184

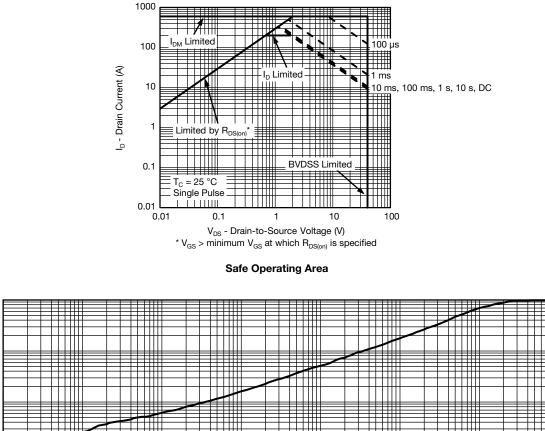


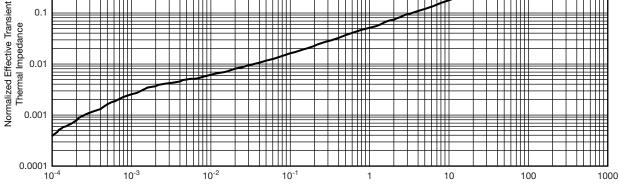
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)





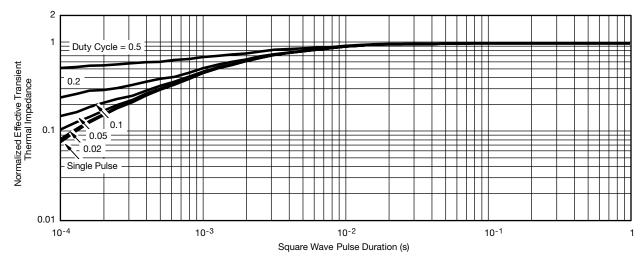
Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67184.



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REVISION	HISTORY ^a	
REVISION	DATE	DESCRIPTION OF CHANGE
В	04-Aug-15	Revised R _g minimum limit

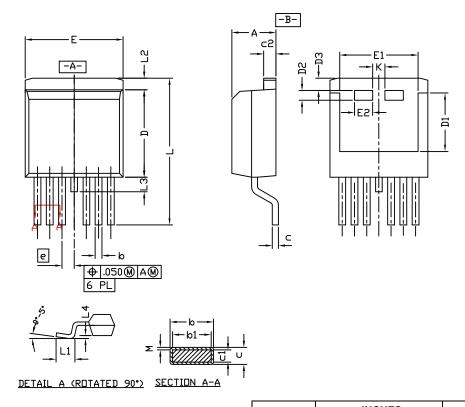
Note

a. As of April 2014



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D²PAK (TO-263-7L) Case Outline



Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

	INCHES		MILLIMETERS		
DIM.	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c* SUB	0.012	0.018	0.305	0.457	
c* SUM	0.022	0.028	0.559	0.711	
c1	0.018	0.025	0.457	0.635	
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.072	0.078	1.829	1.981	
е	0.050	BSC	1.27 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
М	-	0.002	-	0.050	
ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006					

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